

# Microstructure Evolution During Alternating-Current Induced Fatigue

R. R. Keller, R. H. Geiss, Y. –W. Cheng, and D. T. Read  
Materials Reliability Division, NIST, Boulder, CO 80305

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Cyclic Thermomechanical Stresses in Thin Films  
Experimental  
SEM and *Quasi in-situ* EBSD Results  
Analysis of Thin Film Deformation  
Implications on Reliability

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National Semiconductor Metrology Program, NIST Office of Microelectronics Programs  
R. Mönig (MIT), C. Volkert (Forschungszentrum Karlsruhe)

# Cyclic Thermomechanical Stresses

## – Need for Research

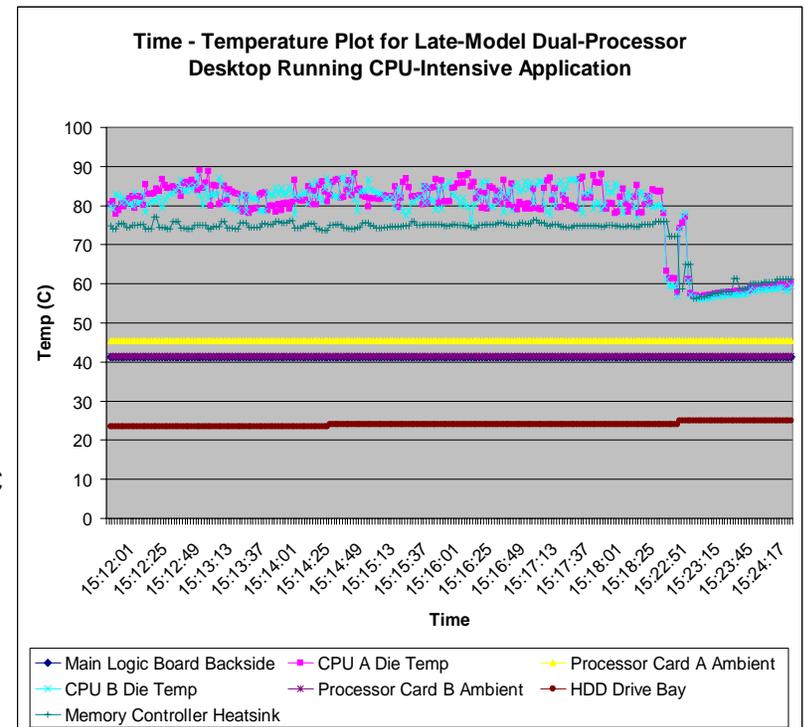
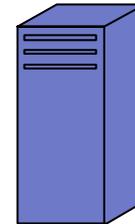
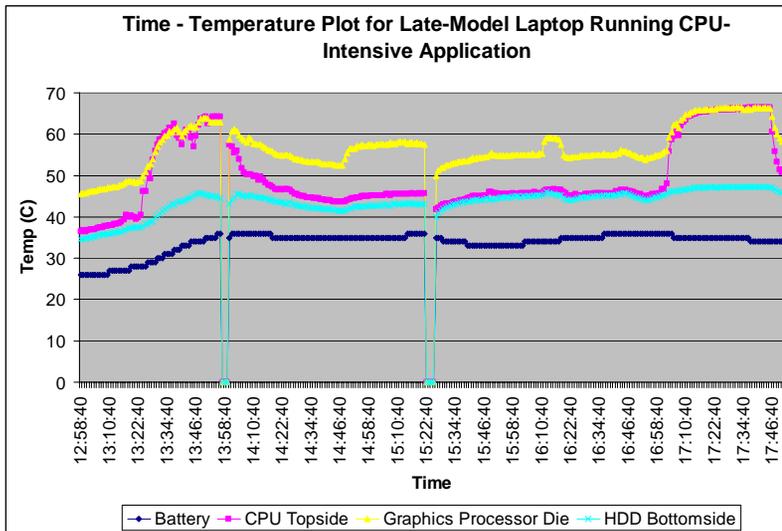
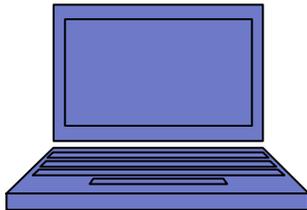
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- *As identified by 2003 ITRS, 2004 NIST Workshop on Reliability Issues in Nanomaterials:*
  - Thermomechanical fatigue in chip- and package-level interconnect systems is a genuine concern for future generations
  - Detecting, testing, modeling, and control of failure mechanisms is necessary
    - **We address these concerns.**

# Cyclic Thermomechanical Stresses

## – Real-world Examples

□ *Big temperature excursions!*



↑  
↓  
 $\Delta T \sim 50^{\circ}\text{C}$

# Experimental

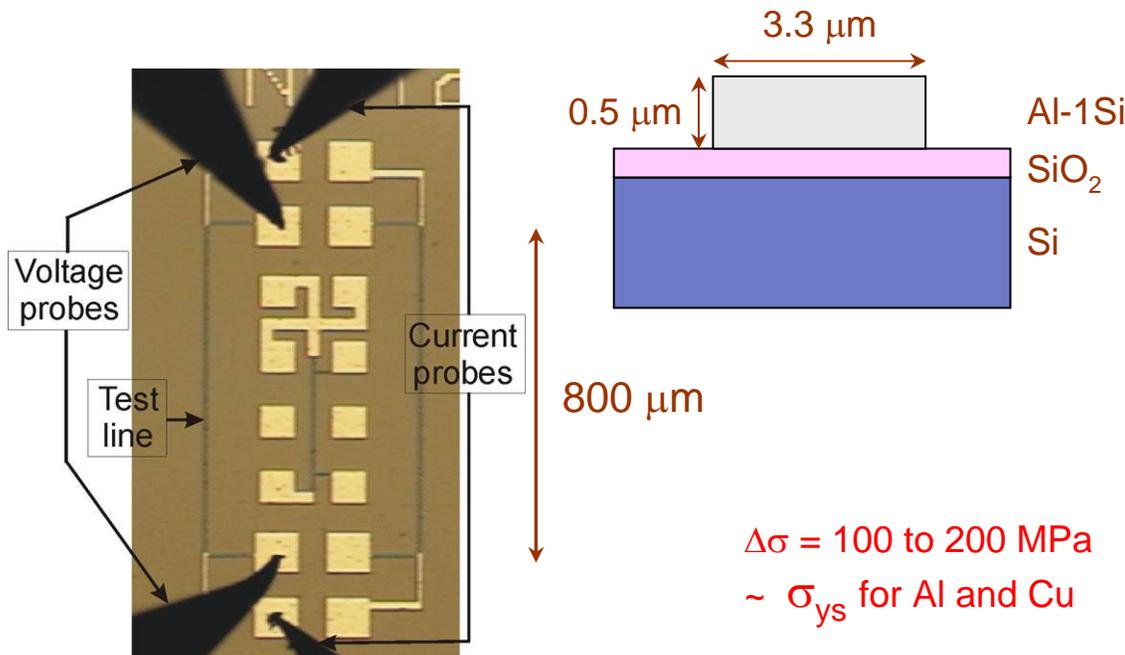
## – Time-varying Electrical Stressing

- Thermomechanical fatigue testing
- 4-point probe method
- Low frequency, high current density,  $j$
- Controlled Joule heating

R. Mönig, R. R. Keller, C. A. Volkert,  
*Rev. Sci. Instrum.* 75, 4997, (2004).

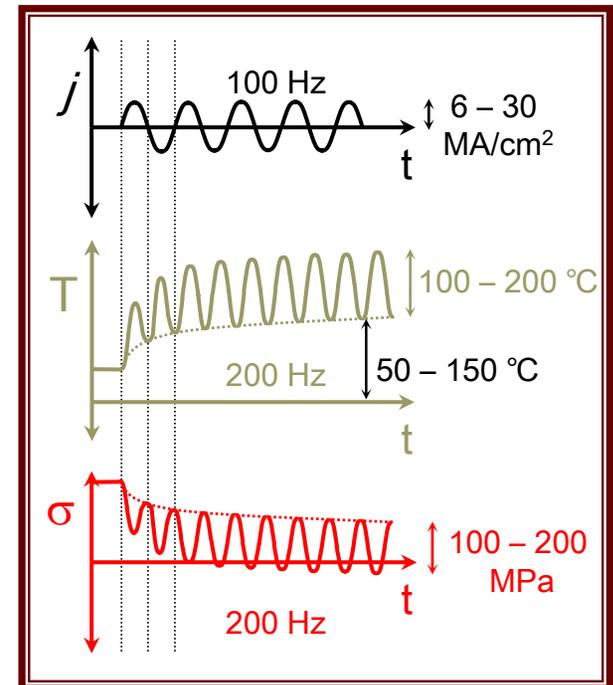
$$\varepsilon_{\text{thermal}} = \Delta\alpha \Delta T (= 0.002 \text{ for Al})$$

(between metal and substrate)



$$\Delta\sigma = 100 \text{ to } 200 \text{ MPa}$$

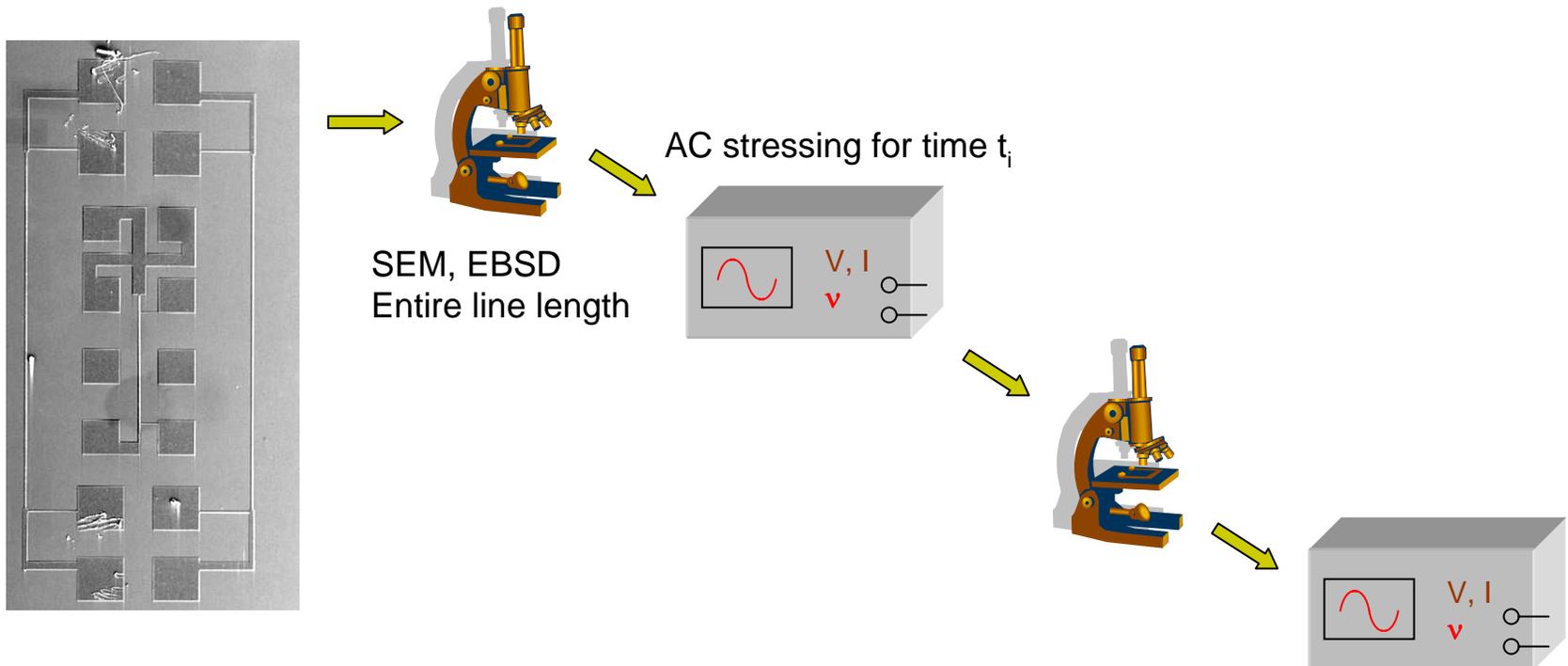
$$\sim \sigma_{\text{ys}} \text{ for Al and Cu}$$



# Experimental

## – *Quasi in-situ* Electron Backscatter Diffraction

- *Observe, test, observe, test, ... , monitoring of one specimen:*
- *Observed after  $t = 0, 10, 20, 40, 80, 160, 320$ , failure (697) s of accumulated stressing time.*

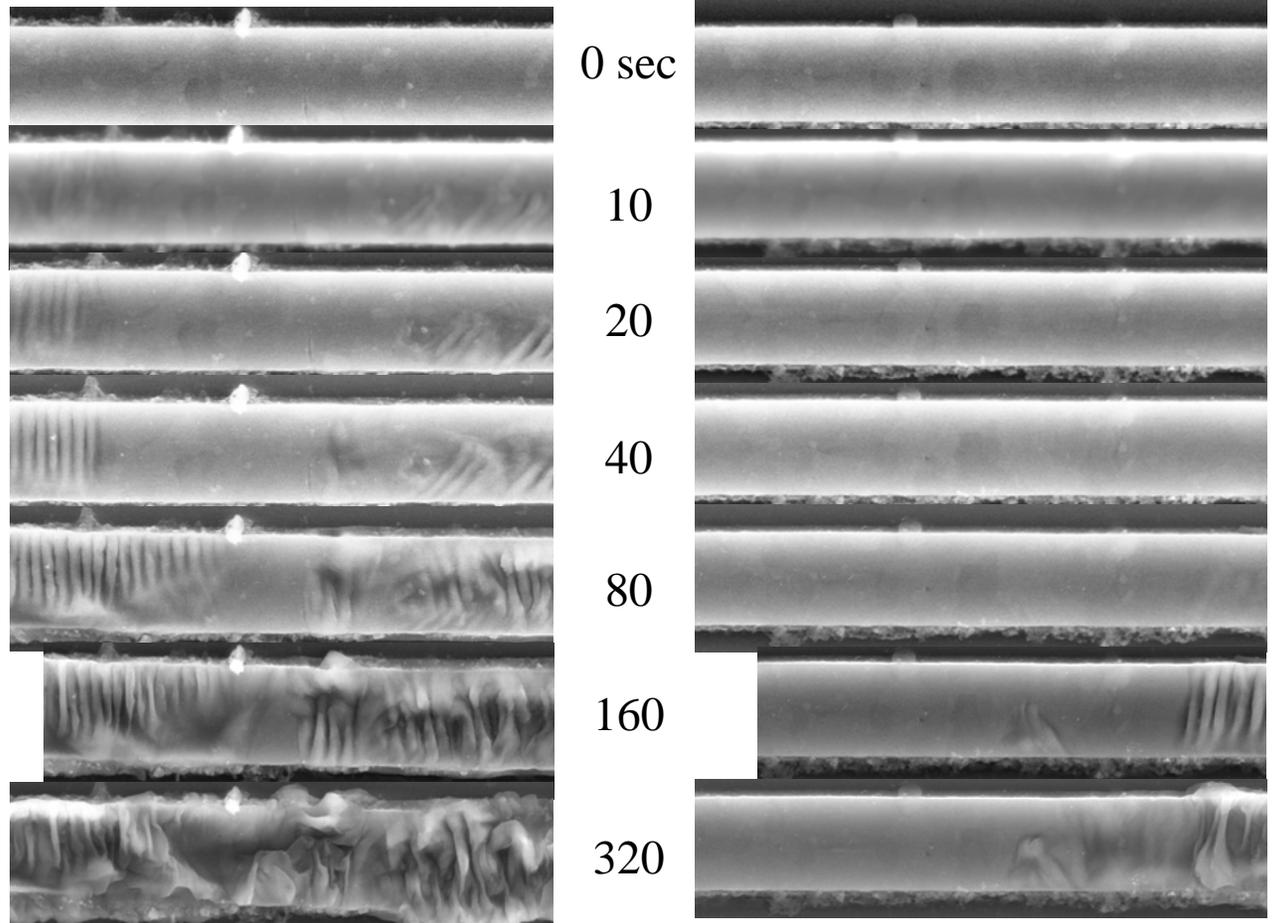


# Results – Damage Evolution (SEM)

- *Surface damage highly localized:*

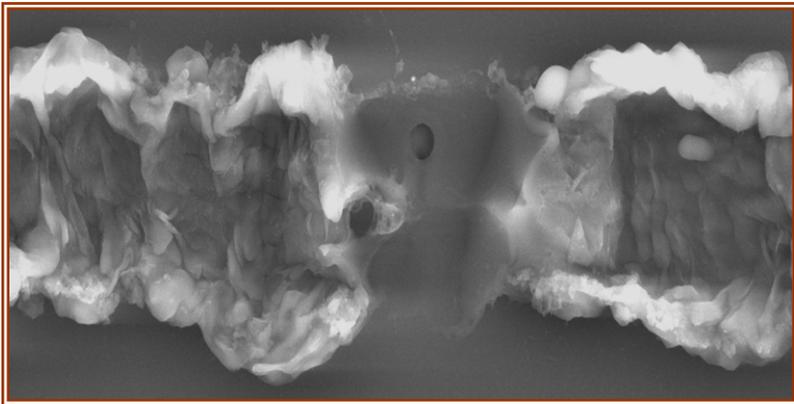
Plan-view SE images  
Linewidth = 3.3  $\mu\text{m}$

Progressive damage,  
typical of fatigue.

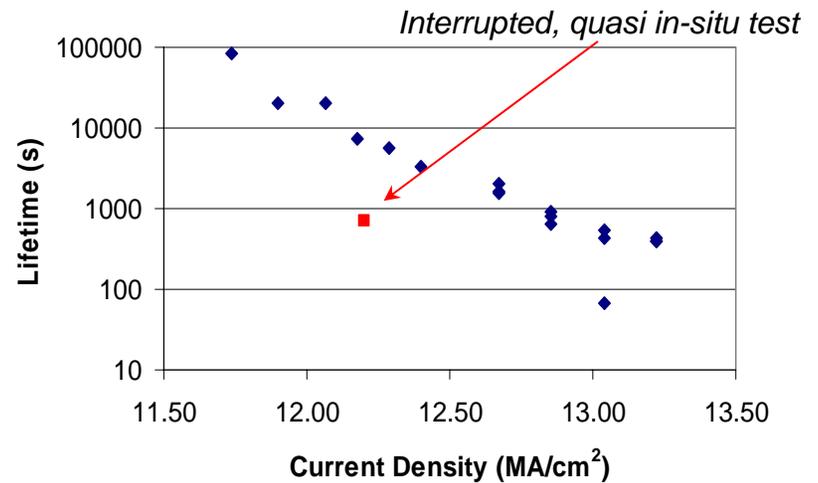


# Results – Final Failure

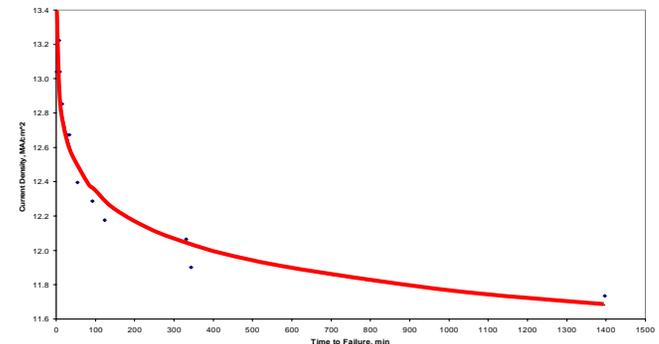
*Open circuit at 697 s:*



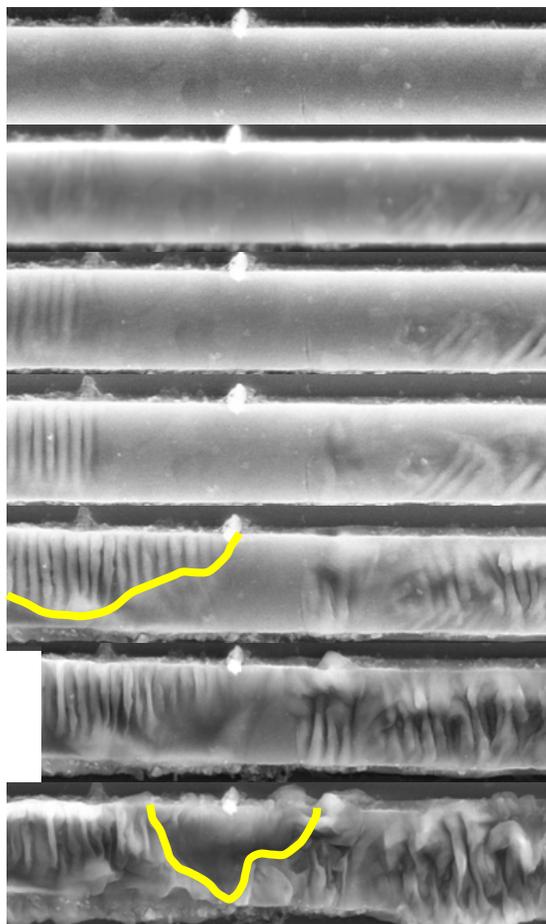
*Lifetime data:*



*Similar to fatigue S-N curve:*



# Results – Damage Evolution (SEM + EBSD)



0 sec



10



20



40



80



160

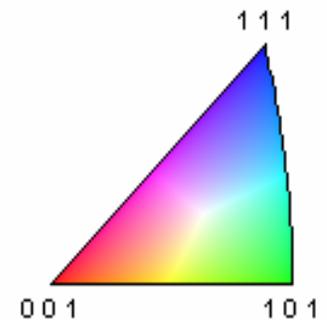


320



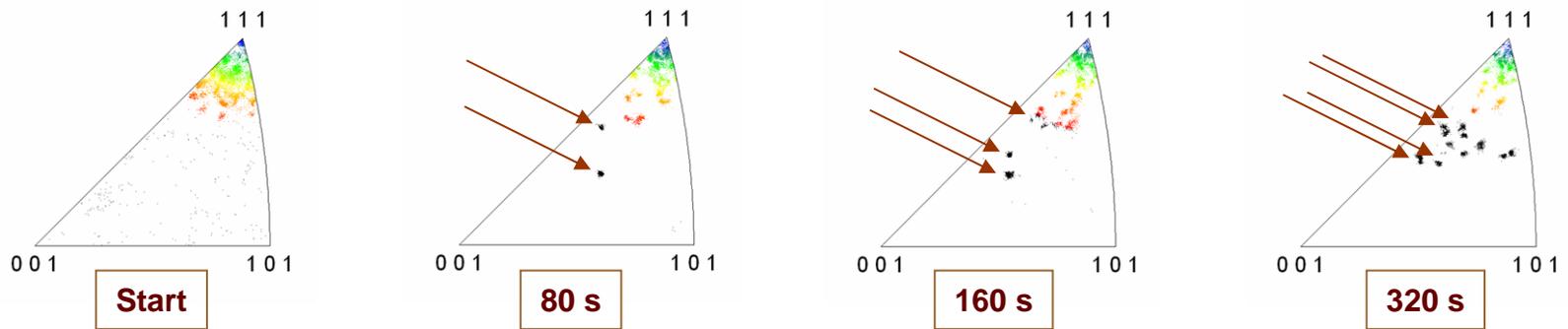
Damage localization corresponds to grain structure.

Growth of damage corresponds to growth and re-orientation of grains!

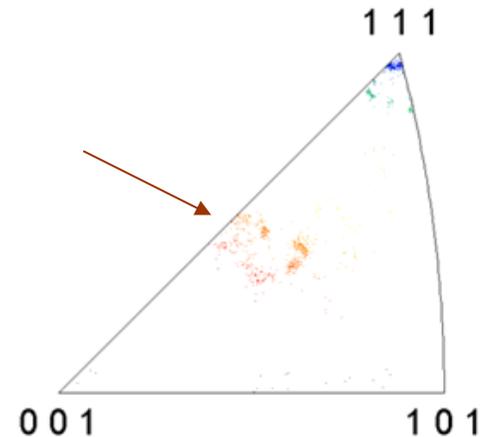
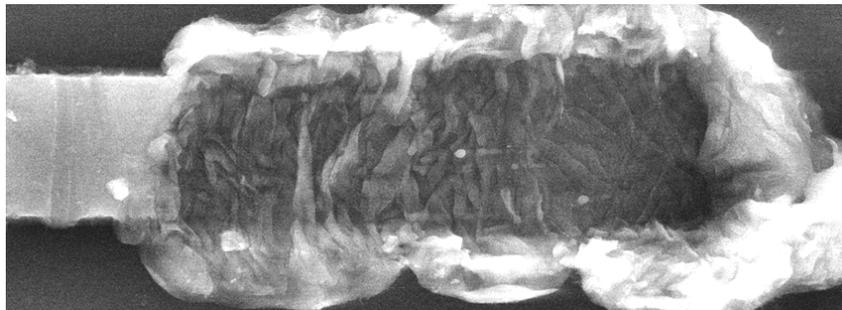


# Results – Grain Re-orientation

- *Surface normals move away from  $\langle 111 \rangle$  with stressing:*

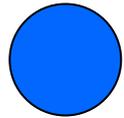


Severely deformed area:

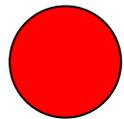


# Re-orientation Summary for Entire Line

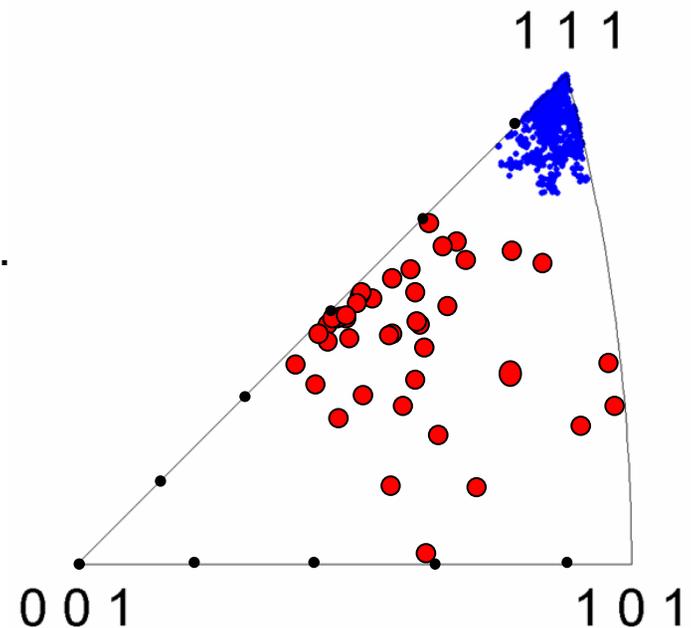
- *All severely deformed areas show drastic re-orientation*
- *Sometimes in excess of 35°!*



As-deposited starting normal orientations.  
Within 10 degrees of (111).



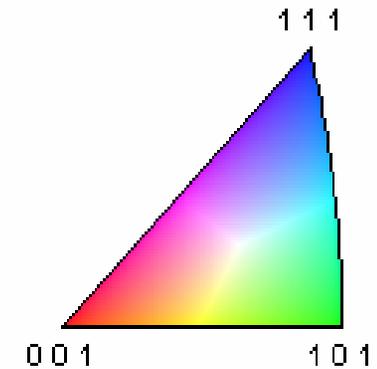
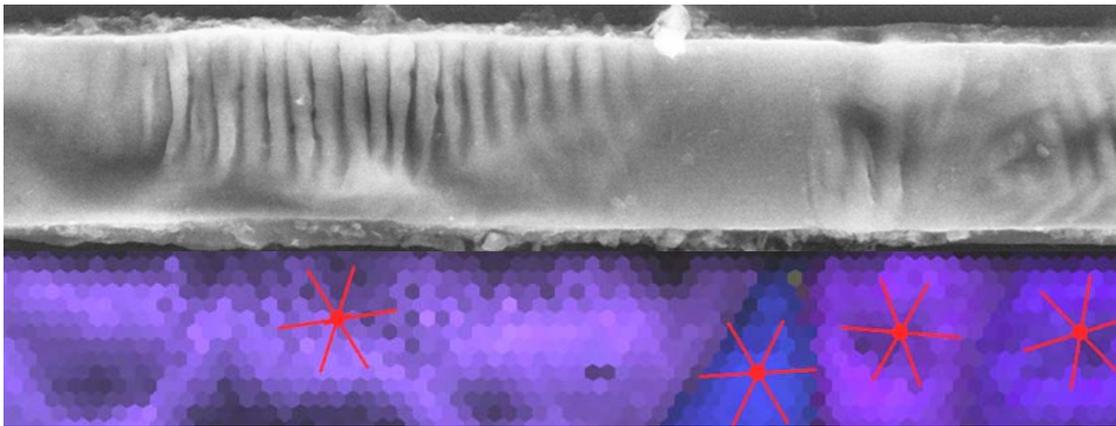
New normal orientation of severely  
deformed structures after failure.



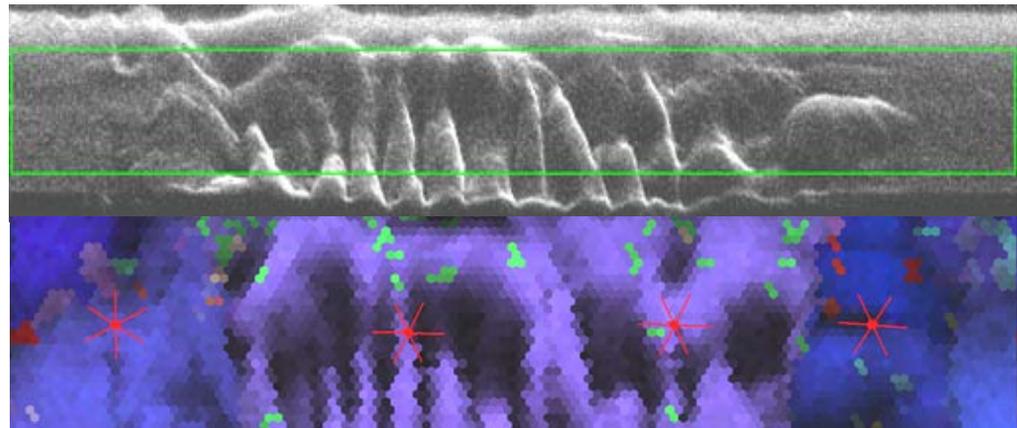
# Analysis

## – Damage by Dislocation Processes

- *Topography consistent with multiple slip:*

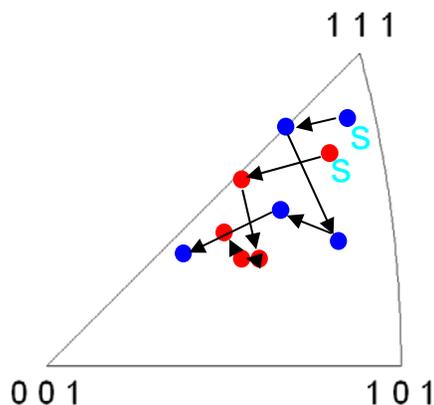
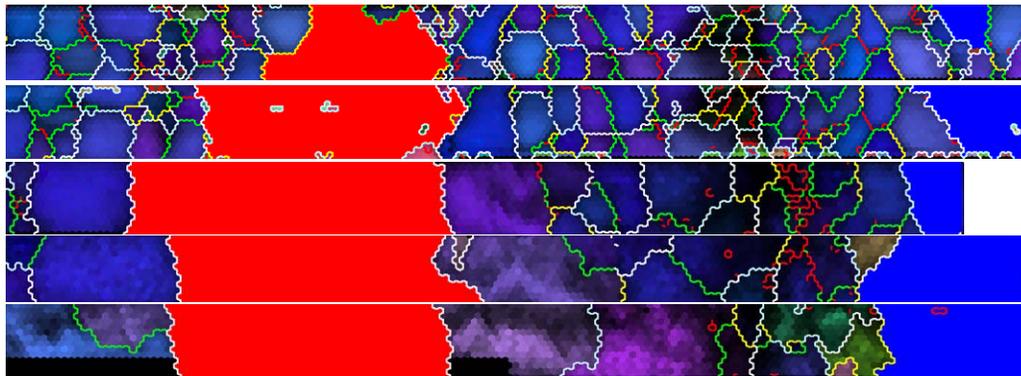


denotes (111) slip traces



# Analysis – Progression of Re-orientation with Cycling

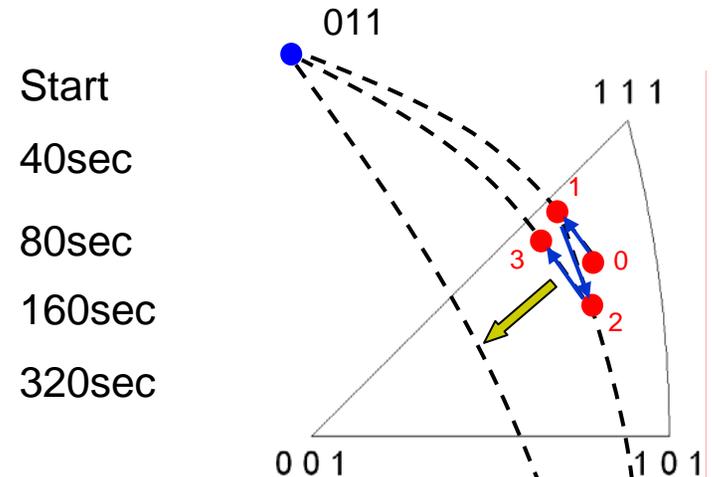
- Surface normals move away from (111)



- Irreversible rotation accumulated during cycling.
- Extent depends upon magnitude of  $\tau_{CRSS}$  and number of cycles.
- Net rotation can amount to tens of degrees.

ASME IMECE 2004, Anaheim, CA

primary slip direction (tension)

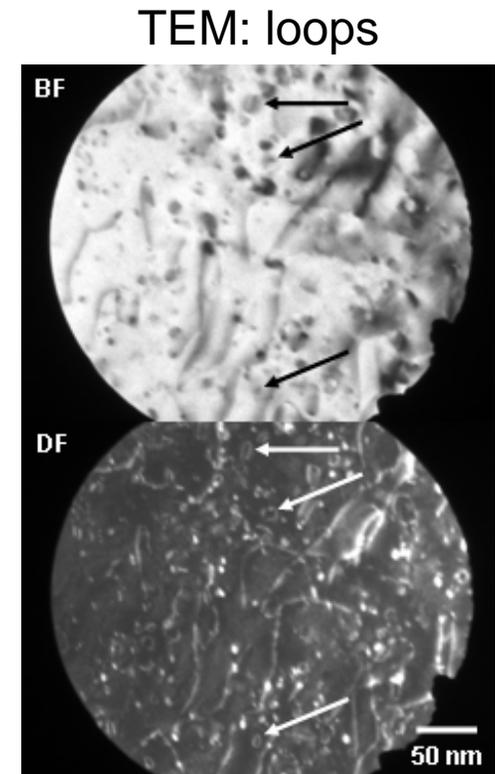


Adapted from:  
Li, Li, Zhang, Wang, and Lu,  
*Phil. Mag.* **A82**, 3129 (2002).

normal to primary  
slip plane (compression)

# Temperature

- *Recrystallization?*
  - No!
  - 50%  $T_{\text{recrystallization}}$  (1 h) ~ 240 to 320 °C
  - Prismatic loops  $\Rightarrow$  sustained  $T_{\text{max}} < \sim 150$  °C
  - Consistent with time-resolved R
  - More deformation with increased cycling: inconsistent with new grains.
- Higher average temperature: may be safer from thermomechanical fatigue point of view
  - Lower R ratio, lower stress
- *However! Can form whiskers...*



# Characteristic Diffusion Distances

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- *Distance estimate:*

$$x = \sqrt{Dt}$$

$t = 0.005$  s in one temperature cycle

	$D$ (m <sup>2</sup> /s)	$x$
<i>Grain Boundary</i>	$10^{-15}$	<i>1.5 nm</i>
<i>Lattice</i>	$10^{-18}$	<i>0.05 nm</i>
<i>Thermal</i>	$10^{-4}$	<i>500 μm</i>

# Reliability

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- *Electromigration: Negligible!*
  - $t$  (1/2 current cycle) = 0.005 s:
    - total diffusion distance ~1 nm or less
  
- *Passivation integrity: Depends...*
  - Compliant dielectric (hard-baked photoresist) does *nothing* to suppress damage;
  - Rigid, poorly adhering dielectric (nitride) bowed and delaminated;
  - Rigid, well adhering dielectric (oxide): in progress.
    - Expect damage to be suppressed.

# Summary

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- *Developing electrical-based test method for thermomechanical fatigue of patterned structures;*
  - Based on controlled Joule heating;
- *Observed highly selective damage formation;*
  - Dependent on grain structure;
- *Damage:*
  - Severe surface topography;
  - Grain growth;
  - Grain re-orientation;
- *Reliability issues?*

*Thank you so much!*